

Docket No. 211897US99

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

IN RE APPLICATION OF: Robert J. HIGGINS, et al.

SERIAL NO: 09/911,496

GAU: 2814

FILED: July 25, 2001

EXAMINER: WILLE

FOR: MONOLITHIC SEMICONDUCTOR-PIEZOELECTRIC DEVICE STRUCTURES AND ELECTRO-ACOUSTIC  
CHARGE TRANSPORT DEVICES



**INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97**

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

Applicant(s) wish to disclose the following information.

**REFERENCES**

- The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references were submitted in application Serial No. 09/908,888 according to the attached copy of a Granted Petition. This application contains related subject matter.
- A check is attached in the amount required under 37 CFR §1.17(p).

**RELATED CASES**

- Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- A check is attached in the amount required under 37 CFR §1.17(p).

**CERTIFICATION**

- Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

**DEPOSIT ACCOUNT**

- Please charge any additional fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,  
MAIER & NEUSTADT, P.C.  


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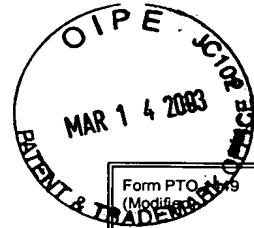
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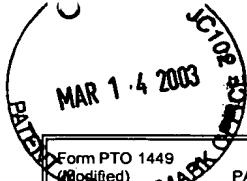
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Form PTO 1449 (Revised)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 211897US99	SERIAL NO. 09/911,496		
LIST OF REFERENCES CITED BY APPLICANT  MAR 14 2003		APPLICANT		Robert J. HIGGINS, et al.			
		FILING DATE		July 25, 2001			
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
AA		3,802,967	04/09/74	Ladany et al.			
AB		4,174,422	11/13/79	Matthews et al.			
AC		4,404,265	09/13/83	Manasevit			
AD		4,482,906	11/13/84	Hovel et al.			
AE		4,523,211	06/11/85	Morimoto et al.			
AF		4,661,176	04/28/87	Manasevit			
AG		4,793,872	12/27/88	Meunier et al.			
AH		4,846,926	07/11/89	Kay et al.			
AJ		4,855,249	08/08/89	Akasaki et al.			
AI		4,891,091	01/02/90	Shastry			
AK		4,912,087	03/27/90	Aslam et al.			
AL		4,928,154	05/22/90	Umeno et al.			
AM		4,963,949	10/16/90	Wanlass et al.			
AN		5,141,894	08/25/92	Bisaro et al.			
AO		5,159,413	10/27/92	Calviello et al.			
AP		5,173,474	12/22/92	Connell et al.			
AQ		5,221,367	06/22/93	Chisholm et al.			
AR		5,225,031	07/06/93	McKee et al.			
AS		5,358,925	10/25/94	Neville Connell et al.			
AT		5,393,352	02/28/95	Summerfelt			
AU		5,418,216	05/23/95	Fork			
AV		5,450,812	09/19/95	McKee et al.			
AW		5,478,653	12/26/95	Guenzer			
AX		5,482,003	01/09/96	McKee et al.			
AY		5,514,484	05/07/96	Nashimoto			
AZ		5,556,463	09/17/96	Guenzer			
BA		5,588,995	12/31/96	Sheldon			
BB		5,670,798	09/23/97	Schetzina			
BC		5,733,641	03/31/98	Fork et al.			
BD		5,735,949	04/07/98	Mantl et al.			
BE		5,741,724	04/21/98	Ramdani et al.			
BF		5,810,923	09/22/98	Yano et al.			
BG		5,830,270	11/03/98	McKee et al.			
BH		5,912,068	06/15/99	Jia			
BI		6,020,222	02/01/00	Wollesen			
BJ		6,045,626	04/04/00	Yano et al.			
BK		6,064,078	05/16/00	Northrup et al.			
BL		6,064,092	05/16/00	Park			
BM		6,096,584	08/01/00	Ellis-Monaghan et al.			
BN		6,103,008	08/15/00	McKee et al.			
BO		6,136,666	10/24/00	So			
BP		6,174,755	01/16/01	Manning			
BQ		6,180,486	01/30/01	Leobandung et al.			

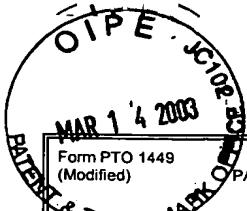
Form PTO 1449 (Modified)			U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO. 211897US99	SERIAL NO. 09/911,496	
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			July 25, 2001	2814		
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EXAMINER'S INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
CA	3,766,370	10/16/73	Walther			
CB	4,006,989	02/08/77	Andringa			
CC	4,284,329	08/18/81	Smith et al.			
CD	4,777,613	10/11/98	Shahan et al.			
CE	4,802,182	01/31/89	Thornton et al.			
CF	4,882,300	11/21/89	Inoue et al.			
CG	4,896,194	01/23/90	Suzuki			
CH	4,999,842	03/12/91	Huang et al.			
CI	5,081,062	01/14/92	Vasudev et al.			
CJ	5,155,658	10/13/92	Inam et al.			
CK	5,248,564	09/28/93	Ramesh			
CL	5,260,394	11/09/93	Tazaki et al.			
CM	5,270,298	12/14/93	Ramesh			
CN	5,286,985	02/15/94	Taddiken			
CO	5,310,707	05/10/94	Oishi et al.			
CP	5,326,721	07/05/94	Summerfelt			
CQ	5,404,581	04/04/95	Honjo			
CR	5,418,389	05/23/95	Watanabe			
CS	5,436,759	07/25/95	Dijaii et al.			
CT	5,576,879	11/19/96	Nashimoto			
CU	5,606,184	02/25/97	Abrokawah, et al.			
CV	5,640,267	06/17/97	May et al.			
CW	5,674,366	10/07/97	Hayashi et al.			
CX	5,729,641	03/17/98	Chandonnet et al.			
CY	5,790,583	08/04/98	Ho			
CZ	5,825,799	10/20/98	Ho et al.			
DA	5,857,049	01/05/99	Beranek et al.			
DB	5,874,860	02/23/99	Brunel et al.			
DC	5,926,496	07/20/99	Ho et al.			
DD	5,937,285	08/10/99	Abrokawah, et al.			
DE	5,981,400	11/09/99	Lo			
DF	5,990,495	11/23/99	Ohba			
DG	6,002,375	12/14/99	Corman et al.			
DH	6,008,762	12/28/99	Nghiem			
DI	6,055,179	04/25/00	Koganei et al.			
DJ	6,107,653	08/22/00	Fitzgerald			
DK	6,113,690	09/05/00	Yu et al.			
DL	6,114,996	09/05/00	Nghiem			
DM	6,121,642	09/19/00	Newns			
DN	6,128,178	10/03/00	Newns			
DO	6,143,072	11/07/00	McKee et al.			
DP	6,184,144	02/06/01	Lo			
DQ	6,222,654	04/24/01	Frigo			



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EA	4,484,332	11/20/84	Hawrylo				
EB	4,815,084	03/21/89	Scifres et al.				
EC	4,876,219	10/24/89	Eshita et al.				
ED	4,963,508	10/16/90	Umeno et al.				
EE	5,060,031	10/22/91	Abrokwah, et al.				
EF	5,063,166	11/05/91	Mooney et al.				
EG	5,116,461	05/26/92	Lebby et al.				
EH	5,127,067	06/30/92	Delcoco et al.				
EI	5,144,409	09/01/92	Ma				
EJ	5,293,050	03/08/94	Chapple-Sokol et al				
EK	5,356,831	10/18/94	Calviello et al.				
EL	5,391,515	02/21/95	Kao et al.				
EM	5,442,191	08/15/95	Ma				
EN	5,444,016	08/22/95	Abrokwah, et al.				
EO	5,480,829	01/02/96	Abrokwah, et al.				
EP	5,528,414	06/18/96	Oakley				
EQ	5,614,739	03/25/97	Abrokwah et al.				
ER	5,729,394	03/17/98	Sevier et al.				
ES	5,731,220	03/24/98	Tsu et al.				
ET	5,764,676	06/09/98	Paoli et al.				
EU	5,777,762	07/07/98	Yamamoto				
EV	5,778,018	07/07/98	Yoshikawa et al.				
EW	5,778,116	07/07/98	Tomich				
EX	5,801,105	09/01/98	Yano et al.				
EY	5,828,080	10/27/98	Yano et al.				
EZ	5,858,814	01/12/99	Goossen et al.				
FA	5,861,966	01/19/99	Ortel				
FB	5,883,996	03/16/99	Knapp et al.				
FC	5,995,359	11/30/99	Klee et al.				
FD	6,058,131	05/02/00	Pan				
FE	6,137,603	10/24/00	Henmi				
FF	6,146,906	11/14/00	Inoue et al.				
FG	6,173,474	01/16/01	Conrad				
FH	6,180,252	01/30/01	Farrell et al.				
FI	4,242,595	12/30/0	Lehovec				
FJ	4,398,342	08/16/83	Pitt et al.				
FK	4,424,589	01/03/84	Thomas et al.				
FL	4,876,208	10/24/89	Gustafson et al.				
FM	4,482,422	11/84	McGinn et al.				
FN	4,667,088	05/19/87	Kramer				
FO	4,772,929	09/20/88	Manchester et al.				
FP	4,841,775	06/27/89	Ikeda et al.				
FQ	4,845,044	07/04/89	Ariyoshi et al.				



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		<b>U.S. PATENT DOCUMENTS</b>			
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
GA	4,868,376	09/19/89	Lessin et al.		
GB	4,885,376	12/05/89	Verkade		
GC	4,888,202	12/89	Murakami et al.		
GD	4,891,091	12/90	Wanlass et al.		
GE	5,051,790	09/24/91	Hammer		
GF	5,055,445	10/08/91	Belt et al.		
GG	5,081,519	11/14/92	Nishimura et al.		
GH	5,143,854	09/01/92	Pirring et al.		
GI	5,185,589	02/09/93	Krishnaswamy et al.		
GJ	5,191,625	03/02/93	Gustavsson		
GK	5,194,397	03/16/93	Cook et al.		
GL	5,208,182	05/04/93	Narayan et al.		
GM	5,216,729	06/01/93	Berger et al.		
GN	5,314,547	05/24/94	Heremans et al.		
GO	5,352,926	10/04/94	Andrews		
GP	5,356,509	10/18/94	Terranova et al.		
GQ	5,371,734	12/06/94	Fischer		
GR	5,372,992	12/94	Itozaki et al.		
GS	5,405,802	04/11/95	Yamagata et al.		
GT	5,442,561	08/15/95	Yoshizawa et al.		
GU	5,453,727	09/26/95	Shibasaki et al.		
GV	5,466,631	11/14/95	Ichikawa et al.		
GW	5,473,047	12/05/95	Shi		
GX	5,473,171	12/95	Summerfelt		
GY	5,479,033	12/26/95	Baca et al.		
GZ	5,486,406	01/23/96	Shi		
HA	5,491,461	02/13/96	Partin et al.		
HB	5,492,859	02/20/96	Sakaguchi et al.		
HC	5,494,711	02/27/96	Takeda et al.		
HD	5,504,035	04/02/96	Rostoker et al.		
HE	5,504,183	04/02/96	Shi		
HF	5,511,238	04/23/96	Bayraktaroglu		
HG	5,512,773	04/96	Wolf et al.		
HH	5,515,047	05/07/96	Yamakido et al.		
HI	5,515,810	05/14/96	Yamashita et al.		
HJ	5,519,235	05/96	Ramesh		
HK	5,549,977	08/96	Jin et al.		
HL	5,551,238	09/03/96	Pruett		
HM	5,552,547	09/03/96	Shi		
HN	5,589,284	12/31/96	Summerfelt et al.		
HO	5,602,418	02/11/97	Imai et al.		
HP	5,633,724	05/27/97	King et al.		



Form PTO 1449 (Modified)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO. 211897US99	SERIAL NO. 09/911,496
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Robert J. HIGGINS, et al.	
		FILING DATE July 25, 2001	GROUP 2814

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
IA	5,650,646	07/22/97	Summerfelt			
IB	5,656,382	08/12/97	Nashimoto			
IC	5,659,180	08/19/97	Shen et al.			
ID	5,661,112	08/26/97	Hatta et al.			
IE	5,679,965	11/95	Schetzina			
IF	5,725,641	03/10/98	MacLeod			
IG	5,745,631	04/28/98	Reinker			
IH	5,776,621	07/07/98	Nashimoto			
II	5,777,350	07/07/98	Nakamura et al.			
IJ	5,789,845	08/04/98	Wadaka et al.			
IK	5,792,569	08/11/98	Sun et al.			
IL	5,792,679	08/11/98	Nakato			
IM	5,796,648	08/18/98	Kawakubo et al.			
IN	5,801,072	09/01/98	Barber			
IO	5,812,272	09/22/98	King et al.			
IP	5,814,583	09/98	Itozaki et al.			
IQ	5,825,055	10/20/98	Summerfelt			
IR	5,827,755	10/27/98	Yonchara et al.			
IS	5,833,603	11/10/98	Kovacs et al.			
IT	5,838,035	11/17/98	Ramesh			
IU	5,844,260	12/01/98	Ohori			
IV	5,846,846	12/08/98	Suh et al.			
IW	5,863,326	01/26/99	Nause et al.			
IX	5,872,493	02/16/99	Ella			
IY	5,879,956	03/99	Seon et al.			
IZ	5,880,452	03/09/99	Plesko			
JA	5,883,564	03/16/99	Partin			
JB	5,907,792	05/25/99	Droopad et al.			
JC	5,937,274	08/10/99	Kondow et al.			
JD	5,948,161	09/07/99	Kizuki			
JE	5,959,879	09/28/99	Koo			
JF	5,966,323	10/99	Chen et al.			
JG	5,987,011	11/16/99	Toh			
JH	6,022,140	02/08/00	Fraden et al.			
JI	6,022,410	02/08/00	Yu et al.			
JJ	6,023,082	02/08/00	McKee et al.			
JK	6,028,853	02/22/00	Haartsen			
JL	6,049,702	04/11/00	Tham et al.			
JM	6,078,717	06/20/00	Nashimoto et al			
JN	6,088,216	07/00	Laibowitz et al.			
JO	6,090,659	07/00	Laibowitz et al.			
JP	6,107,721	08/22/00	Lakin			
JQ	6,153,010	11/28/00	Kiyoku et al			

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U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  LIST OF REFERENCES CITED BY APPLICANT		ATTY DOCKET NO. 211897US99		SERIAL NO. 09/911,496	
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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
KA	6,153,454	11/28/00	Krivokapic		
KB	6,191,011	02/01	Gilboa et al		
KC	6,204,737	03/20/01	Ella		
KD	6,224,669	05/01/01	Yi et al.		
KE	6,225,051	05/01/01	Sugiyama et al.		
KF	6,241,821	06/05/01	Yu et al.		
KG	6,265,749	07/24/01	Gardner et al.		
KH	6,313,486	11/01	Kencke et al.		
KI	6,316,832	11/13/01	Tsuzuki et al.		
KJ	2002/0008234	01/02	Emrick		
KK	3,670,213	06/13/72	Nakawaga et al.		
KL	4,756,007	07/05/88	Qureshi et al.		
KM	4,773,063	09/20/88	Hunsperger et al.		
KN	5,394,489	02/28/95	Koch		
KO	5,406,202	04/11/95	Mehrgardt et al.		
KP	5,528,067	06/18/96	Farb et al.		
KQ	5,572,052	11/05/96	Kashihara et al.		
KR	5,767,543	06/16/98	Ooms et al.		
KS	6,175,497	01/16/01	Tseng et al.		
KT	6,197,503	03/06/01	Vo-Dinh et al.		
KU	6,248,459	06/19/01	Wang et al.		
KV	6,252,261	06/26/01	Usui et al.		
KW	6,255,198	07/03/01	Linthicum et al.		
KX	6,268,269	07/31/01	Lee et al.		
KY	6,291,319	09/18/01	Yu et al.		
KZ	6,316,785	11/13/01	Nunoue et al.		
LA	6,343,171	01/29/02	Yoshimura et al.		
LB	4,965,649	10/23/90	Zanio et al.		
LC	6,253,649	05/01	Kawahara et al.		
LD	6,211,096	04/01	Allman et al.		
LE	6,239,449	05/29/01	Fafard et al.		
LF	2001/0013313	08/16/01	Droopad et al.		
LG	6,184,044	02/06/01	Sone et al.		
LH	6,011,646	01/04/00	Mirkarimi et al.		
LI	5,227,196	07/13/93	Itoh		
LJ	6,150,239	11/21/00	Goesele et al.		
LK	5,441,577	08/15/95	Sasaki et al.		
LL	4,459,325	07/10/84	Nozawa et al.		
LM	4,392,297	07/12/83	Little		
LN	4,289,920	09/15/81	Hovel		
LO	5,281,834	01/25/94	Cambou et al.		
LP	4,901,133	02/13/90	Curran et al.		
LQ	5,514,904	05/07/96	Onga et al.		

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U.S. PATENT &amp; TRADEMARK OFFICE

Form PTO 1449  
(Modified)U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

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## APPLICANT

Robert J. HIGGINS, et al.

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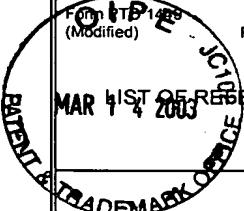
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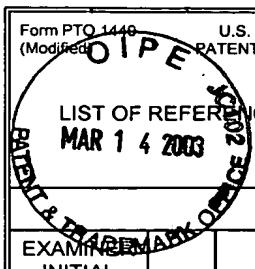
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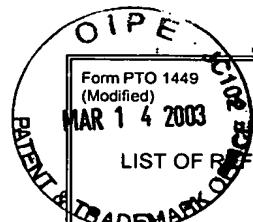
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	MC	6,229,159	05/08/01	Suzuki			
	MD	4,748,485	05/31/88	Vasudev			
	ME	4,984,043	01/08/91	Vinal			
	MF	5,754,319	05/19/98	Van De Voorde et al.			
	MG	6,108,125	08/22/00	Yano			
	MH	5,073,981	12/17/91	Giles et al.			
	MI	5,140,651	08/18/92	Soref et al.			
	MJ	5,610,744	03/11/97	Ho et al.			
	MK	6,362,017	03/26/02	Manabe et al.			
	ML	6,242,686	06/05/01	Kishimoto et al.			
	MM	5,689,123	11/18/97	Major et al.			
	MN	5,670,800	09/23/97	Nakao et al.			
	MO	5,067,809	11/26/91	Tsubota			
	MP	5,596,205	01/21/97	Reedy et al.			
	MQ	6,175,555	01/16/01	Hoole			
	MR	5,357,122	10/18/94	Okubora et al.			
	MS	4,084,130	04/11/78	Holton			
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	MU	6,372,813	04/16/02	Johnson et al.			
	MV	5,608,046	03/04/97	Cook et al.			
	MW	5,955,591	09/21/99	Imbach et al.			
	MX	6,022,963	02/08/00	McGall et al.			
	MY	6,083,697	07/04/00	Beecher et al.			
	MZ	5,063,081	11/05/91	Cozzette et al.			
	NA	5,479,317	12/26/95	Ramesh			
	NB	5,306,649	04/26/94	Hebert			
	NC	5,962,069	10/05/99	Schindler et al.			
	ND	5,541,422	07/30/96	Wolf et al.			
	NE	5,873,977	02/23/99	Desu et al.			
	NF	5,538,941	07/23/96	Findikoglu et al.			
	NG	6,046,464	04/04/00	Schetzina			
	NH	6,235,145	05/22/01	Li et al.			
	NI	5,610,744	03/11/97	Ho et al.			
	NJ	5,280,013	01/18/94	Newman et al.			
	NK	6,348,373 B1	02/19/02	Ma et al.			
	NL	6,339,664 B1	01/15/02	Farjady et al.			
	NM	4,439,014	03/27/84	Stacy et al.			
	NN	4,889,402	12/26/89	Reinhart			
	NO	5,963,291	10/05/99	Wu et al.			
	NP	6,011,641	01/04/00	Shin et al.			
	NQ	6,340,788 B1	01/22/02	King et al.			

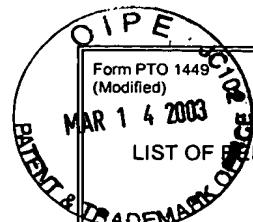
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		APPLICANT Robert J. HIGGINS, et al.			
		FILING DATE July 25, 2001		GROUP 2814	
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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS SUB CLASS
	OA	5,807,440	09/15/98	Kubota et al.	
	OB	4,681,982	07/21/87	Yoshida	
	OC	4,629,821	12/16/86	Bronstein-Bonte et al.	
	OD	4,452,720	06/05/84	Harada et al.	
	OE	3,935,031	01/27/76	Adler	
	OF	5,760,426	06/02/98	Marx et al.	
	OG	5,053,835	10/01/91	Horikawa et al.	
	OH	6,326,645 B1	12/04/01	Kadota	
	OI	5,770,887	06/23/98	Tadatomo et al.	
	OJ	6,372,356 B1	04/16/02	Thornton et al.	
	OK	4,774,205	09/27/88	Choi et al.	
	OL	6,359,330 B1	03/19/02	Goudard	
	OM	5,312,765	05/17/94	Kanber	
	ON	5,734,672	03/31/98	McMinn et al.	
	OO	6,367,699 B2	04/09/02	Ackley	
	OP	5,530,235	06/25/96	Stefik et al.	
	OQ	5,623,552	04/22/97	Lane	
	OR	5,481,102	01/02/96	Hazelrigg, Jr.	
	OS	6,134,114	10/17/00	Ungermann et al.	
	OT	5,984,190	11/16/99	Nevill	
	OU	5,789,733	08/04/98	Jachimowicz et al.	
	OV	5,753,300	05/19/98	Wessels et al.	
	OW	6,208,453	03/27/01	Wessels et al.	
	OX	5,886,867	03/23/99	Chivukula et al.	
	OY	5,028,976	07/02/91	Ozaki et al.	
	OZ	5,869,845	02/09/99	Vander Wagt et al.	
	PA	5,596,214	01/21/97	Endo	
	PB	6,391,674 B2	05/21/02	Ziegler	
	PC	6,275,122 B1	08/14/01	Speidell et al.	
	PD	6,238,946 B1	05/29/01	Ziegler	
	PE	6,210,988 B1	04/03/01	Howe et al.	
	PF	6,392,257	05/21/02	Ramdani et al.	
	PG	4,442,590	04/17/84	Stockton et al.	
	PH	5,603,764	02/18/97	Matsuda et al.	
	PI	6,087,681	06/11/00	Shakuda	
	PJ	5,132,648	07/21/92	Trinh et al.	
	PK	6,427,066	07/30/02	Grube	
	PL	2002/0072245	06/13/02	Ooms et al.	
	PM	6,278,138 B1	08/21/01	Suzuki	
	PN	5,888,296	03/30/99	Ooms et al.	
	PO	5,198,269	03/30/93	Swartz et al.	
	PP	2002/0030246	03/14/02	Eisenbeiser et al.	
	PQ	2002/0047143	04/25/02	Ramdani et al.	

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		FILING DATE July 25, 2001		GROUP 2814		
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QA	5,776,359	07/07/98	Schultz et al.			
QB	5,569,953	10/29/96	Kikkawa et al.			
QC	5,834,362	11/10/98	Miyagaki et al.			
QD	6,248,621 B1	06/19/01	Wilk et al.			
QE	5,266,355	11/30/93	Wernberg et al.			
QF	6,277,436 B1	08/21/01	Stauf et al.			
QG	6,039,803	03/21/00	Fitzgerald et al.			
QH	5,619,051	04/08/97	Endo			
QI	5,420,102	05/30/95	Harshavardhan et al.			
QJ	5,210,763	05/11/93	Lewis et al.			
QK	5,103,494	04/07/92	Mozer			
QL	4,594,000	06/10/86	Falk et al.			
QM	4,297,656	10/27/81	Pan			
QN	5,244,818	09/14/93	Jokers et al.			
QO	6,048,751	04/11/00	D'Asaro et al.			
QP	5,484,664	01/16/96	Kitahara et al.			
QQ	5,780,311	07/14/98	Beasom et al.			
QR	6,438,281 B1	08/20/02	Tsukamoto et al.			
QS	5,399,898	03/21/95	Rostoker			
QT	6,271,619	08/07/01	Yamada et al.			
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QV	4,910,164	03/20/90	Shichijo			
QW	4,952,420	08/28/90	Walters			
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QZ	6,143,366	11/07/00	Lu			
RA	6,410,941	06/25/02	Taylor et al.			
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RF	5,516,725	05/14/96	Chang et al.			
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RJ	5,753,928	05/19/98	Krause			
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RM	5,621,227	04/15/97	Joshi			
RN	6,389,209 B1	05/14/02	Suhir			
RO	5,163,118	11/10/92	Lorenzo et al.			
RP	5,926,493	07/20/99	O'Brien et al.			
RQ	5,323,023	06/21/94	Fork			

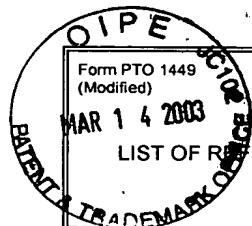
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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	SA	6,156,581	12/05/00	Vaudo et al.			
	SB	5,395,663	03/07/95	Tabata et al.			
	SC	4,146,297	03/27/79	Alfernness et al.			
	SD	5,452,118	09/19/95	Maruska			
	SE	5,889,296	03/30/99	Imamura et al.			
	SF	6,300,615 B1	10/09/01	Shinohara et al.			
	SG	6,232,910 B1	05/15/01	Bell et al.			
	SH	5,686,741	11/11/97	Ohori et al.			
	SI	4,959,702	09/25/90	Moyer et al			
	SJ	6,100,578	08/08/00	Suzuki			
	SK	6,410,947 B1	06/25/02	Wada			
	SL	6,417,059 B2	07/09/02	Huang			
	SM	6,461,927 B1	10/08/02	Mochizuki et al.			
	SN	6,462,360 B1	10/08/02	Higgins, Jr. et al.			
	SO	5,981,976	11/09/99	Murasato			
	SP	5,981,980	11/09/99	Miyajima et al.			
	SQ	2002/0006245 A1	01/17/02	Kubota et al.			
	SR	2002/0131675 A1	09/19/02	Litvin			
	SS	6,256,426 B1	07/03/01	Duchet			
	ST	6,278,523 B1	08/21/01	Gorecki			
	SU	6,319,730 B1	11/20/01	Ramdani et al.			
	SV	6,404,027	06/11/02	Hong et al.			
	SW	6,312,819 B1	11/06/01	Jia et al.			
	SX	5,119,448	06/02/92	Schaefer et al.			
	SY	4,120,588	10/17/78	Chaum			
	SZ	5,194,917	03/16/93	Regener			
	TA	5,018,816	05/28/91	Murray et al.			
	TB	5,953,468	09/14/99	Finnila et al.			
	TC	5,561,305	10/01/96	Smith			
	TD	5,896,476	04/20/99	Wissemann et al.			
	TE	4,934,777	06/19/90	Jou et al.			
	TF	6,320,238 B1	11/20/01	Kizilayali et al.			
	TG	6,393,167 B1	05/21/02	Davis et al.			
	TH	5,760,427	06/02/98	Onda			
	TI	6,411,756 B2	06/25/02	Sadot et al.			
	TJ	5,668,048	09/16/97	Kondo et al.			
	TK	5,852,687	12/22/98	Wickham			
	TL	5,122,852	06/16/92	Chan et al.			
	TM	5,173,835	12/22/92	Cornett et al.			
	TN	5,055,835	10/08/91	Sutton			
	TO	6,139,483	10/31/00	Seabaugh et al.			
	TP	5,283,462	02/01/94	Stengel			
	TQ	6,103,403	08/15/00	Grigorian et al.			



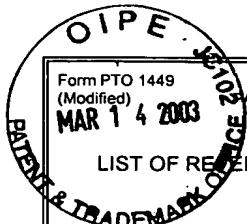
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	UA	5,635,433	06/03/97	Sengupta			
	UB	5,427,988	06/27/95	Sengupta et al.			
	UC	6,297,842 B1	10/02/01	Koizumi et al.			
	UD	5,682,046	10/28/97	Takahashi et al.			
	UE	5,181,085	01/19/93	Moon et al.			
	UF	6,051,858	04/18/00	Uchida et al.			
	UG	6,013,553	01/11/00	Wallace et al.			
	UH	4,872,046	10/03/89	Morkoc et al.			
	UI	2002/0047123 A1	04/25/02	Ramdani et al.			
	UJ	5,995,528	11/30/99	Fukunaga et al.			
	UK	5,075,743	12/24/91	Behfar-Rad			
	UL	5,438,584	08/01/95	Paoli et al.			
	UM	4,503,540	03/05/85	Nakashima et al.			
	UN	5,373,166	12/13/94	Buchan et al.			
	UO	6,278,137 B1	08/21/01	Shimoyama et al.			
	UP	5,623,439	04/22/97	Gotoh et al.			
	UQ	4,981,714	01/01/91	Ohno et al.			
	UR	6,194,753 B1	02/27/01	Seon et al.			
	US	6,326,637 B1	12/04/01	Parkin et al.			
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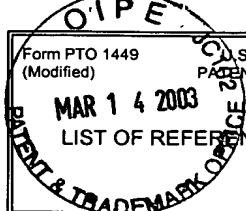
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AAA	0 250 171	12/23/87	EP	X
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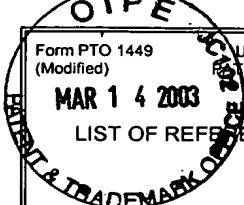


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BAB	2000-068466	03/00	Japan (Abstract)		
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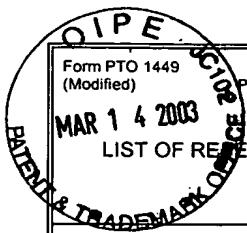
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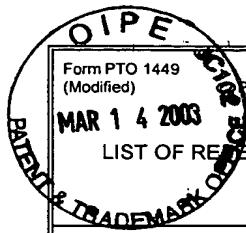
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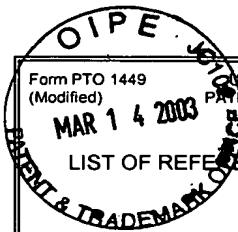
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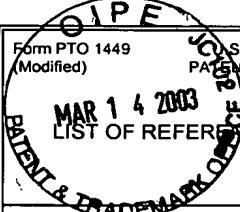
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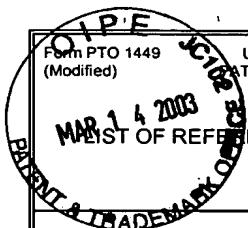
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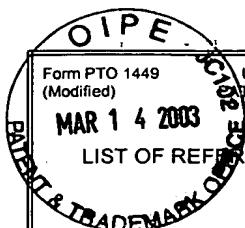
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